



#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	$80m\Omega$ @ $V_{GS}=10V$	3.5A
60 V	150mΩ @ V <sub>GS</sub> =4.5V	2.5A

#### **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

#### **Features and Benefits**

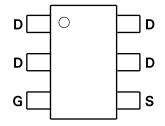
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available

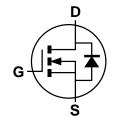
#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.018 grams (Approximate)









Top View

Pin Out - Top View

**Equivalent Circuit** 

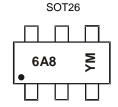
#### Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Quantity per reel
ZXMN6A08E6QTA	Automotive	SOT26	3,000

Note:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



6A8 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н	ı		J
	•											
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

(	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 7)		3.5	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	l <sub>D</sub>	2.8	Α
		(Note 6)		2.8	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 8)	I <sub>DM</sub>	16	Α
Continuous Source Current (Body diode) (Note 7)		I <sub>S</sub>	2.6	Α	
Pulsed Source Current (Bod	y diode)	(Note 8)	I <sub>SM</sub>	16	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)		1.1 8.8	W
Linear Derating Factor	(Note 7)	P <sub>D</sub>	1.7 13.6	mW/°C
Thermal Desistance Junction to Ambient	(Note 6)	D.	113	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	73	- C/VV
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

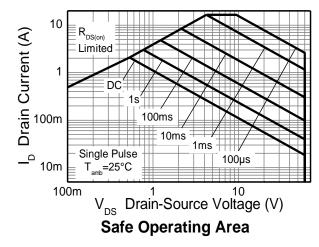
<sup>6.</sup> For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

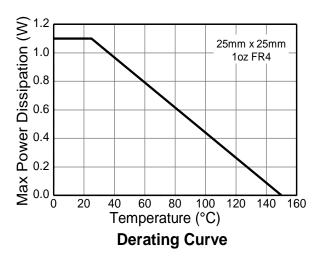
7. Same as Note 6, except the device is measured at t ≤ 10 seconds.

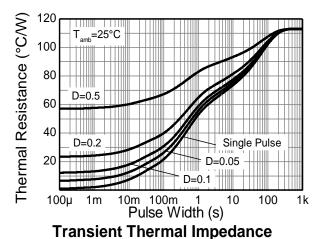
8. Same as Note 6, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.

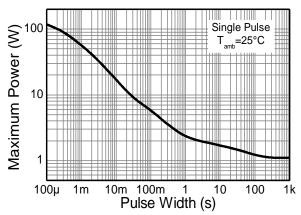


## **Thermal Characteristics**









**Pulse Power Dissipation** 



## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

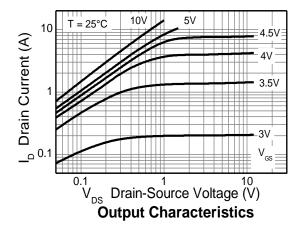
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	0.5	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS				•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	_	_	V	$I_D = 250\mu A$ , $V_{DS} = V_{GS}$	
Static Dunin Course On Benistance (Nets O)	Б		0.067	0.08	0	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.8A	
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>	_	0.1	0.15	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.2A	
Forward Transconductance (Notes 9 & 10)	<b>g</b> fs	_	6.6	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4.8A	
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	_	0.88	1.2	V	I <sub>S</sub> = 4A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	19.2	_	ns	$I_F = 1.4A$ , $di/dt = 100A/\mu s$ ,	
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	_	30.3	_	nC	T <sub>J</sub> = +25°C	
DYNAMIC CHARACTERISTICS (Note 10)	•		•	•	•		
Input Capacitance	C <sub>iss</sub>		459	_	pF		
Output Capacitance	Coss	_	44.2	_	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V -f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	24.1	_	pF	-1 = 11VII 12	
Total Gate Charge (Note 11)	Qg	_	3.7	_	nC	V <sub>GS</sub> = 4.5V	
Total Gate Charge (Note 11)	Qg	_	5.8	_	nC	V <sub>DS</sub> = 30V	
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	_	1.4	_	nC	$V_{GS} = 10V$ $I_{D} = 1.4A$	
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	_	1.9	_	nC	]	
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	2.6	_	ns		
Turn-On Rise Time (Note 11)	tr		2.1	_	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V	
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	12.3	_	ns	$I_D=1.5A,~R_G\cong 6\Omega$	
Turn-Off Fall Time (Note 11)	t <sub>f</sub>		4.6	_	ns		

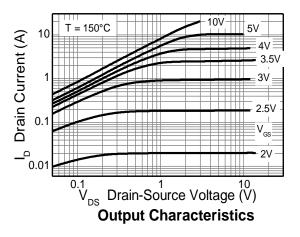
Notes:

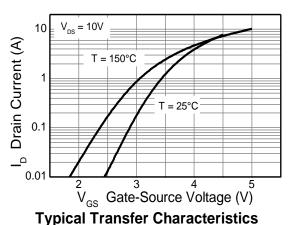
<sup>9.</sup> Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.

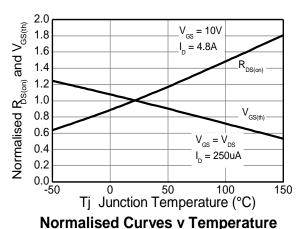


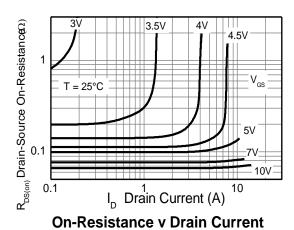
## **Typical Characteristics**

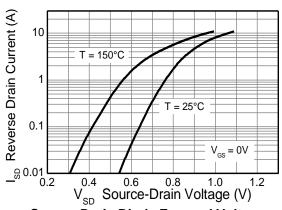








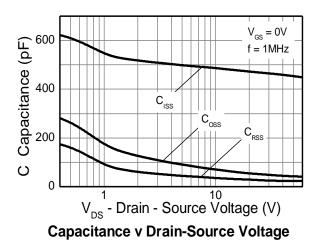


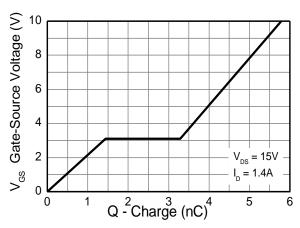


Source-Drain Diode Forward Voltage



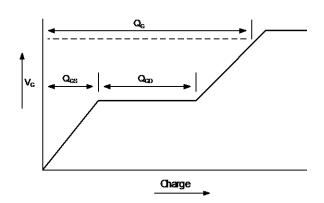
## Typical Characteristics (cont.)



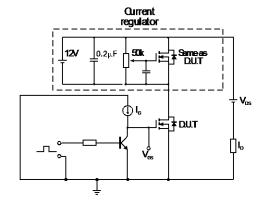


**Gate-Source Voltage v Gate Charge** 

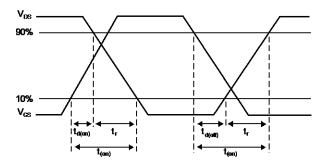
#### **Test Circuits**



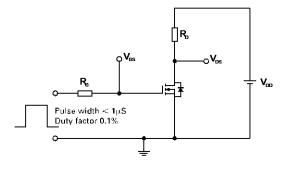
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

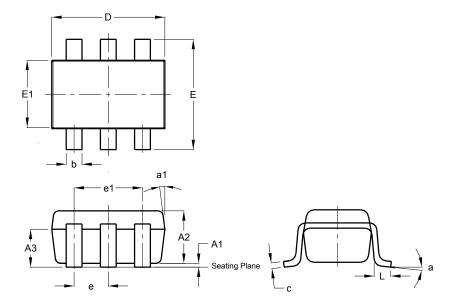


Switching time test circuit



## **Package Outline Dimensions**

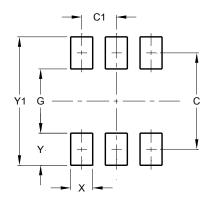
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26						
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
А3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
С	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	-	-	0.95			
e1	-	-	1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а	-	-	8°			
a1	-	-	7°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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